



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23-3L Plastic-Encapsulate Transistors

2SC2735 TRANSISTOR (NPN)

FEATURES

Power dissipation

$$P_{CM}: 0.15 \text{ W (Tamb=25}^{\circ}\text{C)}$$

Collector current

$$I_{CM}: 0.05 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: 30 \text{ V}$$

Operating and storage junction temperature range

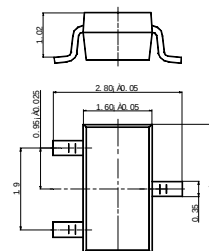
$$T_J, T_{stg}: -55^{\circ}\text{C to } +150^{\circ}\text{C}$$

SOT-23-3L

1. BASE

2. EMITTER

3. COLLECTOR



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	30		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	20		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	3		V
Collector cut-off current	I_{CBO}	$V_{CB}=10V, I_E=0$		0.5	μA
DC current gain	h_{FE}	$V_{CE}=10V, I_C=10mA$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=20mA, I_B=4mA$		1	V
Transition frequency	f_T	$V_{CE}=10V, I_C=10mA$	600		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		1.5	pF
Noise figure	NF	$V_{CC}=12V, I_C=2mA, f=200MHz,$ $f_{osc}=230MHz$		8	dB

Marking	JC
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